

ESD9NA5V

2-Lines, Bi-directional, Transient Voltage Suppressors

<http://www.sh-willsemi.com>

Descriptions

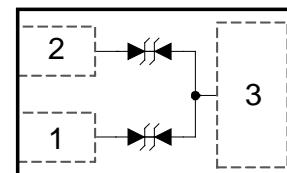
The ESD9NA5V is a bi-directional TVS (Transient Voltage Suppressor). It is specifically designed to protect sensitive electronic components which are connected to low speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning.

The ESD9NA5V may be used to provide ESD protection up to $\pm 30\text{kV}$ (contact and air discharge) according to IEC61000-4-2, and withstand peak pulse current up to 6A (8/20 μs) according to IEC61000-4-5.

The ESD9NA5V is available in DFN1006-3L package. Standard products are Pb-free and Halogen-free.



DFN1006-3L (Bottom View)



Circuit diagram (Top View)



5 = Device code

* = Month code (A~Z)

Marking (Top View)

Order information

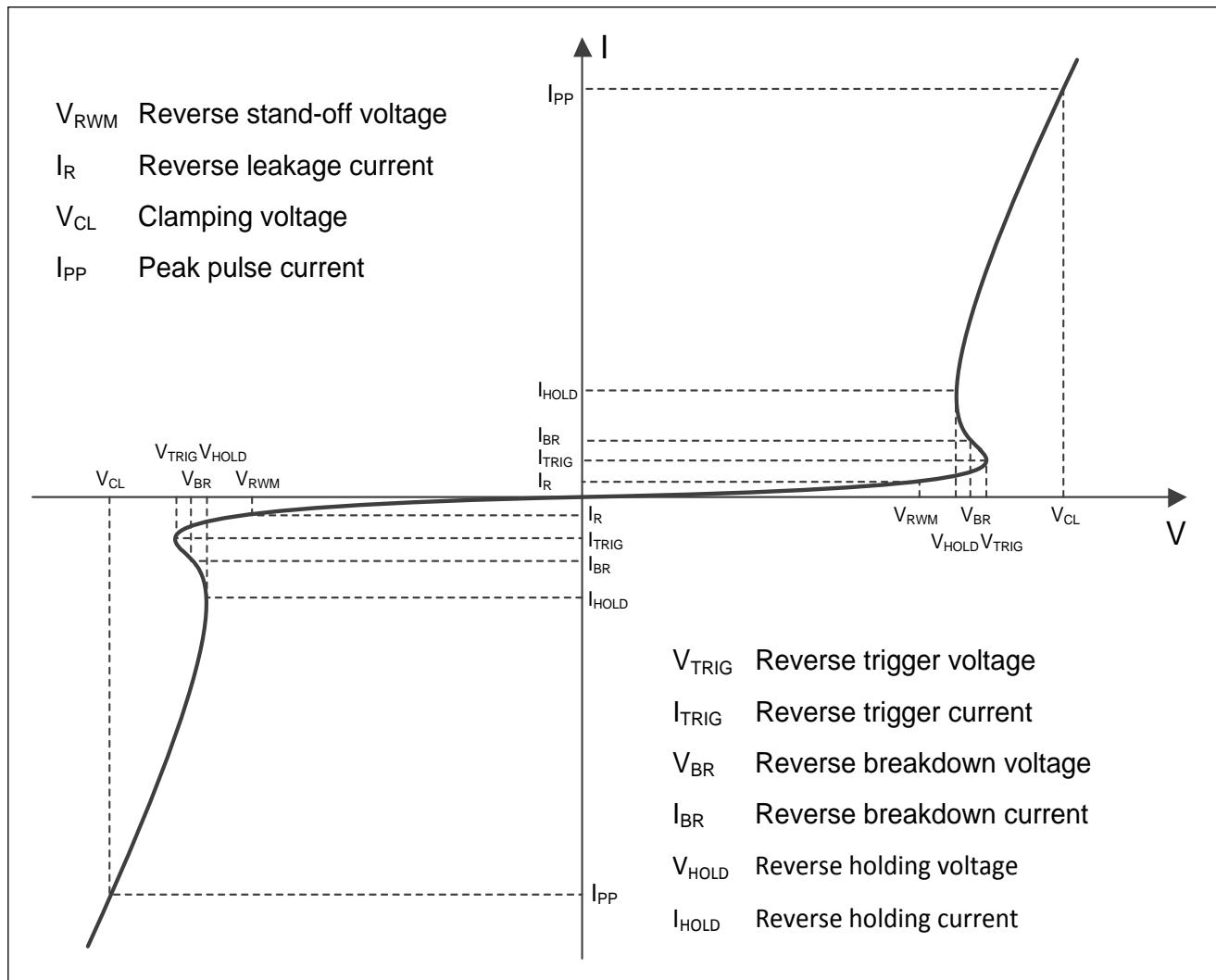
Device	Package	Shipping
ESD9NA5V-3/TR	DFN1006-3L	10000/Tape&Reel

Applications

- Cellular handsets
- Tablets
- Laptops
- Other portable devices
- Network communication devices

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	72	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	6	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	kV
ESD according to IEC61000-4-2 contact discharge		± 30	
Operation junction temperature	T_J	125	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

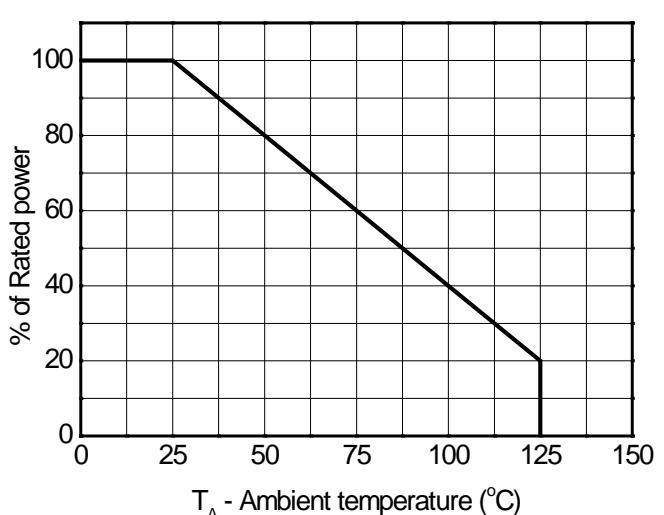
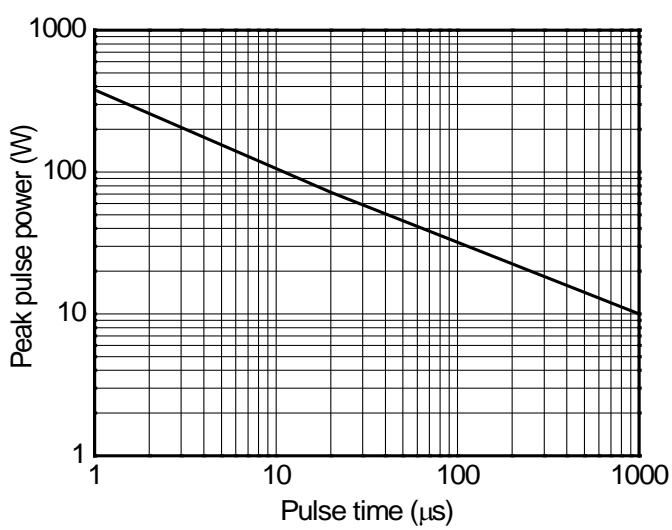
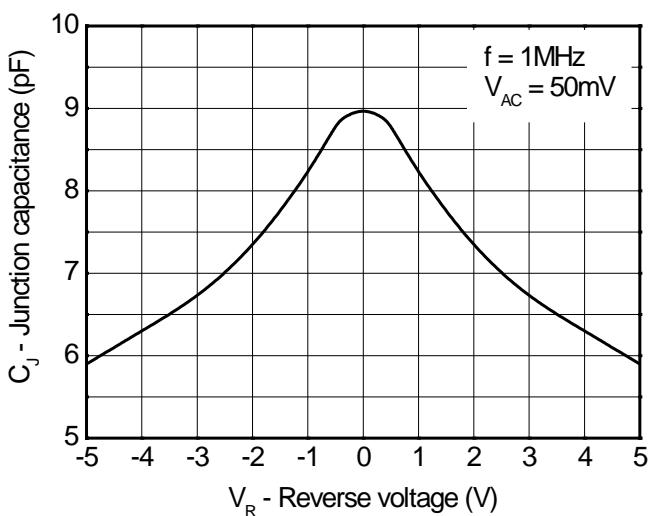
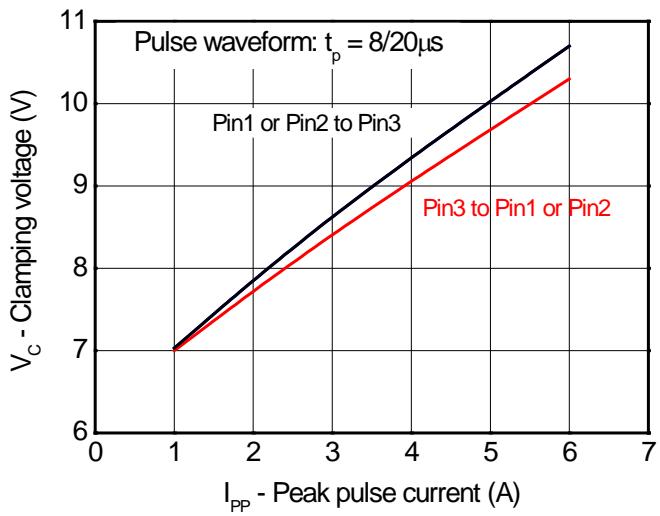
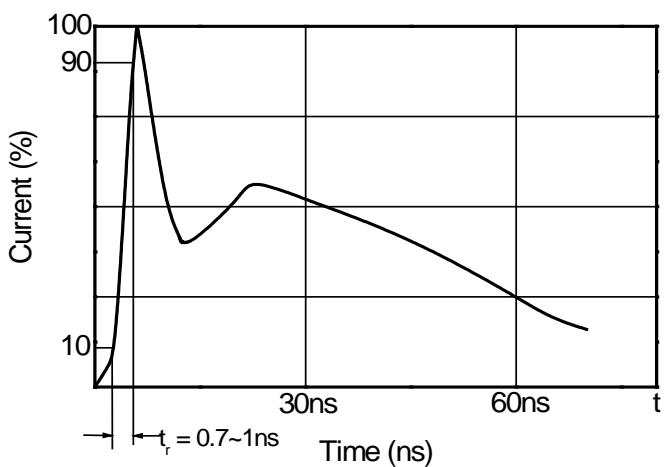
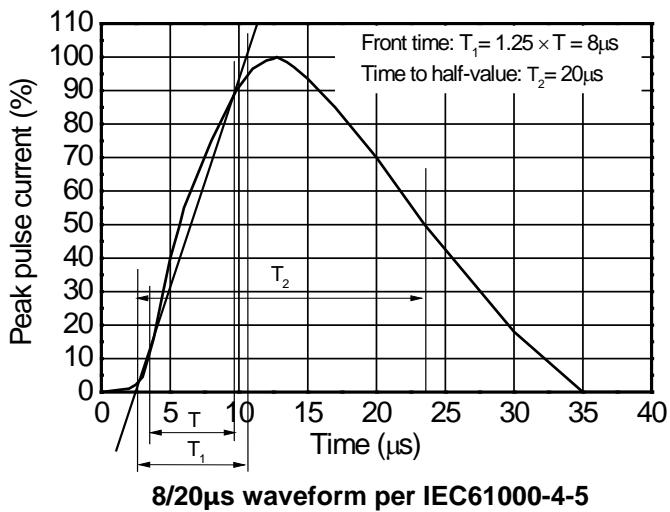
Electrical characteristics ($T_A=25^{\circ}C$, unless otherwise noted)


Electrical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

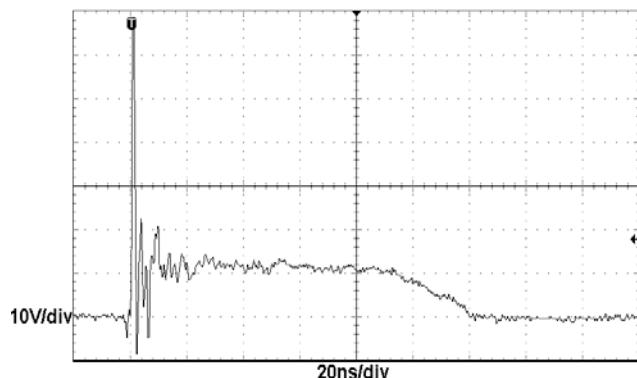
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				± 5	V
Reverse leakage current	I_R	$V_{RWM} = 5\text{V}$			1	μA
Reverse breakdown voltage	V_{BR}	$I_{BR} = 1\text{mA}$	5.1			V
Reverse holding voltage	V_{HOLD}	$I_{HOLD} = 50\text{mA}$	5.1			V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16\text{A}, t_p = 100\text{ns}$		12		V
Clamping voltage ²⁾	V_{CL}	$V_{ESD} = 8\text{kV}$		12		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1\text{A}, t_p = 8/20\mu\text{s}$			8	V
		$I_{PP} = 6\text{A}, t_p = 8/20\mu\text{s}$			12	V
Dynamic resistance ¹⁾	R_{DYN}			0.28		Ω
Junction capacitance	C_J	$V_R = 0\text{V}, f = 1\text{MHz}$ Pin1 or 2 to Pin3		9	12	pF
		$V_R = 0\text{V}, f = 1\text{MHz}$ Between Pin1 and Pin2		5	7	pF

Notes:

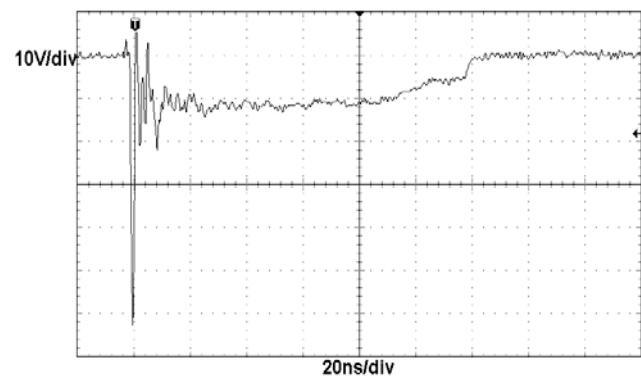
- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)


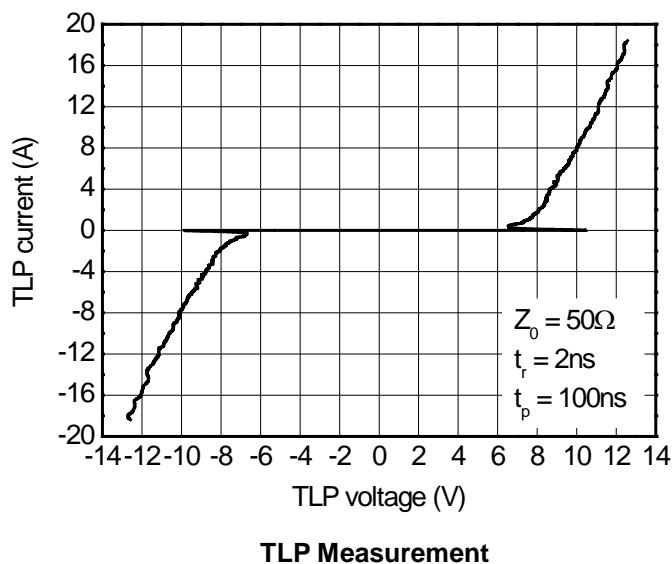
Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)



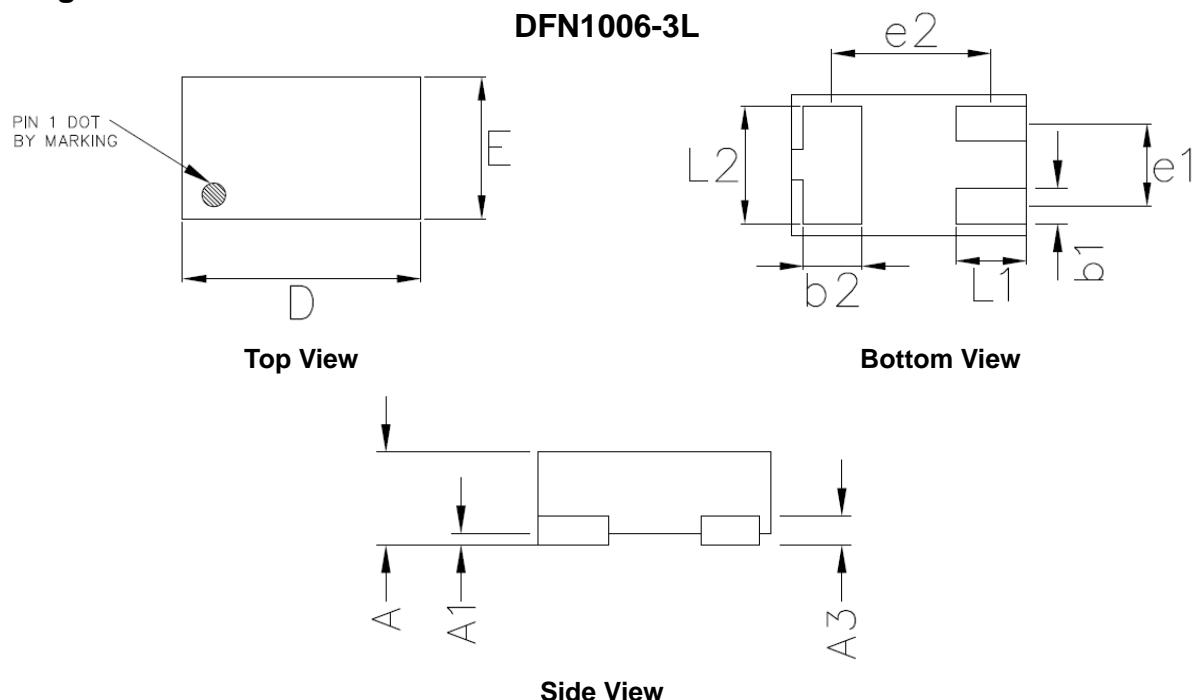
ESD clamping
(+8kV contact discharge per IEC61000-4-2)



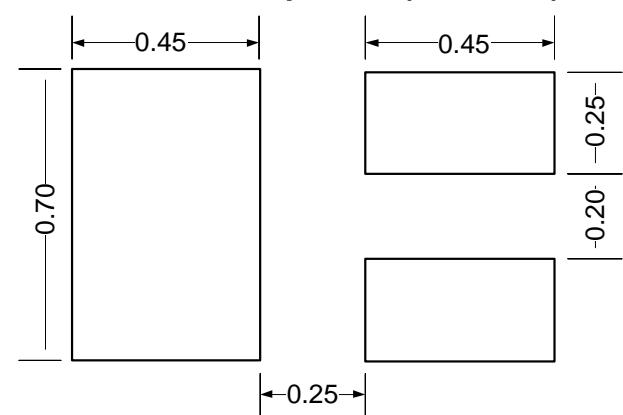
ESD clamping
(-8kV contact discharge per IEC61000-4-2)



TLP Measurement

Package outline dimensions
DFN1006-3L


Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.40	-	0.50
A1	0.00	-	0.05
A3			0.125 REF
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b1	0.10	0.15	0.20
b2	0.20	0.25	0.30
L1	0.20	0.30	0.40
L2	0.40	0.50	0.60
e1	0.350 BSC		
e2	0.675 BSC		

Recommend land pattern (Unit: mm)

Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.